

勝特力電材超市-龍山店 886-3-5773766
 勝特力電材超市-光復店 886-3-5729570
 勝特力電子(上海) 86-21-34970699
 勝特力電子(深圳) 86-755-83298787
<http://www.100y.com.tw>

11N60E

Power MOSFET

PRODUCT SUMMARY	
VDS (V)	650
RDS(on) max. at $V_{GS} = 10\text{ V}$	0.17
Qg max. (nC)	109
Qgs (nC)	15
Qgd (nC)	31
Configuration	Single

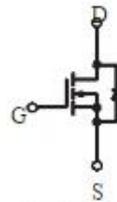
FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



RoHS* Available

TO-220 FULLPAK



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (TC = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	650	V
Gate-Source Voltage	V _{GS}	± 30	V
Continuous Drain Current (T _J = 150 °C)	I _D	V _{GS} at 10 V, TC = 25 °C	20
		TC = 100 °C	13
Pulsed Drain Current ^a	I _{DM}	56	A
Linear Derating Factor		1.8	W/°C
Single Pulse Avalanche Energy ^b	E _{AS}	691	mJ
Maximum Power Dissipation	PD	30	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Drain-Source Voltage Slope	dV/dt	70	V/ns
Reverse Diode dV/dt ^d		26	V/ns
Soldering Recommendations (Peak Temperature) ^c		300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- V_{DD} = 50 V, starting T_J = 25 °C, L = 28 nH, R_{DS(on)} = 45 mΩ.
- 1.6 mm from case.
- I_D = 10 A, dV/dt = 100 A/μs, starting T_J = 25 °C.